

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re PATENT APPLICATION OF

Inventor(s): MIYASHITA et al.

Filed: Herewith

Title: SEMICONDUCTOR DEVICE COMPRISING METAL SILICIDE FILMS FORMED TO COVER GATE ELECTRODE AND SOURCE-DRAIN DIFFUSION LAYERS AND METHOD OF MANUFACTURING THE SAME

July 30, 2001

**PRELIMINARY AMENDMENT**

Hon. Commissioner of Patents  
Washington, D.C. 20231

Sir:

Please amend this application as follows:


**IN THE SPECIFICATION:**

At the top of the first page, just under the title, insert:

1. ☒--This is a ☐ Continuation-In-Part ☒ Divisional  
☐ Continuation ☐ Substitute Application (MPEP 201.09) of  
1(a) ☐ National Application No. 09/164,343 filed October 1, 1998.  
1(b) ☐ International Application No. PCT/\_\_\_/  
filed \_\_\_ which designated the U.S.--
  
2. ☐--This application claims the benefit of U.S. Provisional Application No. 60/\_\_\_, filed \_\_\_--

Respectfully submitted,

PILLSBURY WINTHROP LLP  
Intellectual Property Group

By:   
for Attorney: Glenn J. Perry  
Reg. No: 28,458  
Tel. No.: 703-905-2161  
Fax No.: 703-905-2500

Atty\Sec. GJP/WSE/dae  
1600 Tysons Boulevard  
McLean, VA 22102  
(703) 905-2000